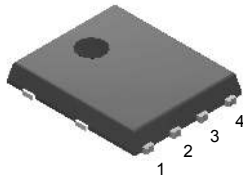
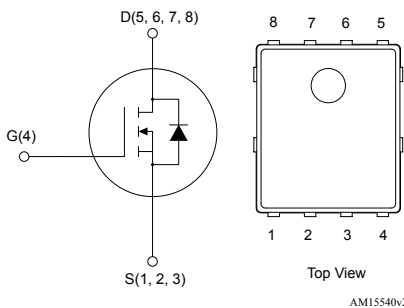



Automotive N-channel 80 V, 5.6 mΩ typ., 95 A, STripFET F7 Power MOSFET in a PowerFLAT 5x6 package


PowerFLAT 5x6


Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STL105N8F7AG	80 V	6.5 mΩ	95 A

- AEC-Q101 qualified 
- Among the lowest $R_{DS(on)}$ on the market
- Excellent FoM (figure of merit)
- Low C_{rSS}/C_{iSS} ratio for EMI immunity
- High avalanche ruggedness
- Wettable flank package

Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.



Product status link

[STL105N8F7AG](#)

Product summary

Order code	STL105N8F7AG
Marking	105N8F7
Package	PowerFLAT 5x6
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	80	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	95	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	68	
$I_{DM}^{(1)}$	Drain current (pulsed)	380	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	127	W
I_{AV}	Avalanche current, repetitive or not repetitive (pulse width limited by maximum junction temperature)	40	A
E_{AS}	Single pulse avalanche energy ($T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AV}$, $V_{DD} = 60\text{ V}$, $R_G \text{ min} = 47\text{ }\Omega$)	135	mJ
T_J	Operating junction temperature range	-55 to 175	$^\circ\text{C}$
T_{stg}	Storage temperature range		$^\circ\text{C}$

1. Pulse width limited by safe operating area.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	1.18	$^\circ\text{C/W}$
$R_{thJB}^{(1)}$	Thermal resistance, junction-to-board	31.3	$^\circ\text{C/W}$

1. When mounted on an FR-4 board of 1 inch², 2oz Cu, $t < 10\text{ s}$.

2 Electrical characteristics

($T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	80			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 80\text{ V}$			1	μA
I_{GSS}	Gate-body leakage current	$V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.5		4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 25\text{ A}$		5.6	6.5	m Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	3475	-	pF
C_{oss}	Output capacitance		-	904	-	pF
C_{rss}	Reverse transfer capacitance		-	88	-	pF
Q_g	Total gate charge	$V_{DD} = 40\text{ V}$, $I_D = 95\text{ A}$,	-	46	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 0\text{ to }10\text{ V}$	-	24	-	nC
Q_{gd}	Gate-drain charge	(see Figure 13. Test circuit for gate charge behavior)	-	10	-	nC

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 40\text{ V}$, $I_D = 50\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	19	-	ns
t_r	Rise time		-	22	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 12. Test circuit for resistive load switching times and Figure 17. Switching time waveform)	-	31	-	ns
t_f	Fall time		-	13	-	ns

Table 6. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				95	A
$V_{SD}^{(1)}$	Source-drain voltage	$I_{SD} = 95\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.2	V
t_{rr}	Reverse recovery time	$I_{SD} = 50\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$,	-	37		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 64\text{ V}$	-	37		nC
I_{RRM}	Reverse recovery current	(see Figure 14. Test circuit for inductive load switching and diode recovery times)	-	1.5		A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

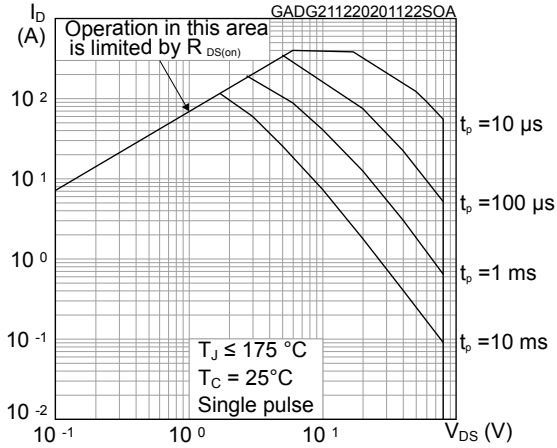


Figure 2. Maximum transient thermal impedance

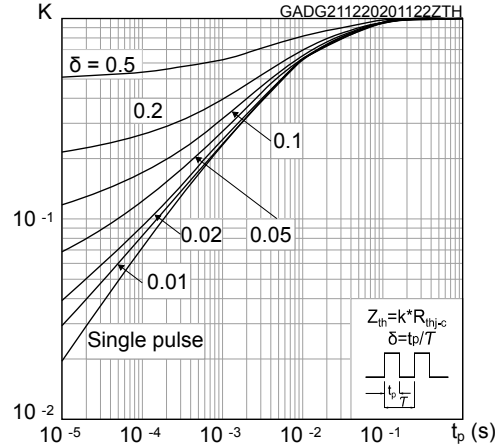


Figure 3. Typical output characteristics

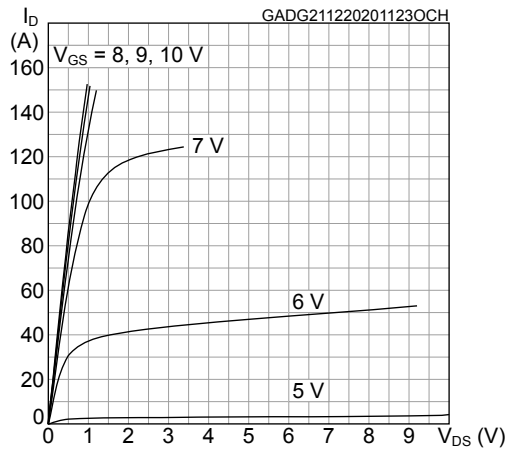


Figure 4. Typical transfer characteristics

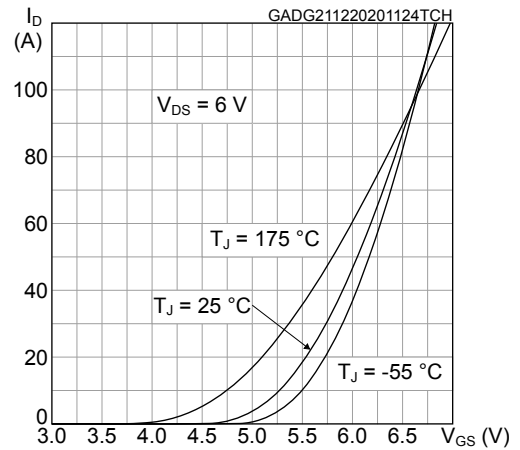


Figure 5. Typical gate charge characteristics

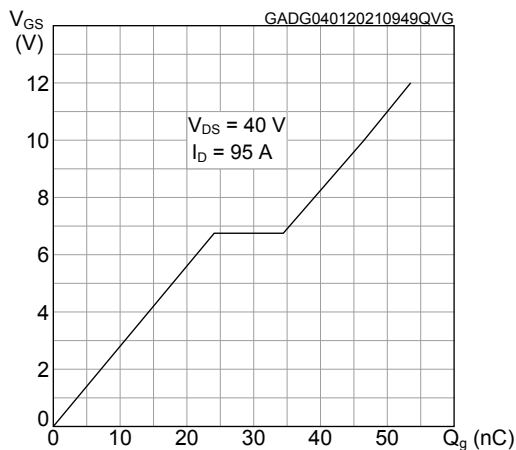


Figure 6. Typical drain-source on-resistance

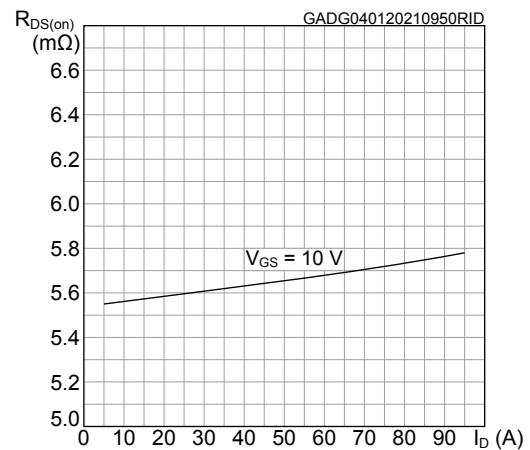


Figure 7. Typical capacitance characteristics

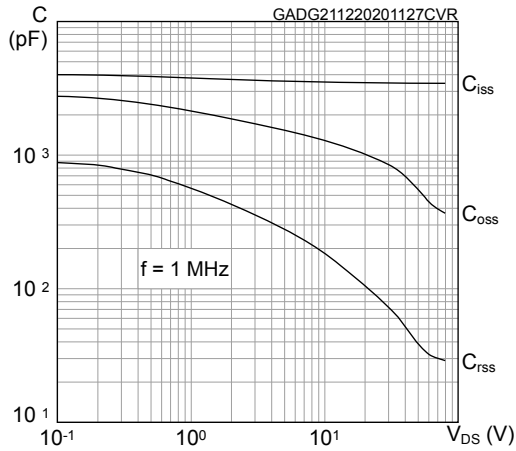


Figure 8. Normalized gate threshold voltage vs temperature

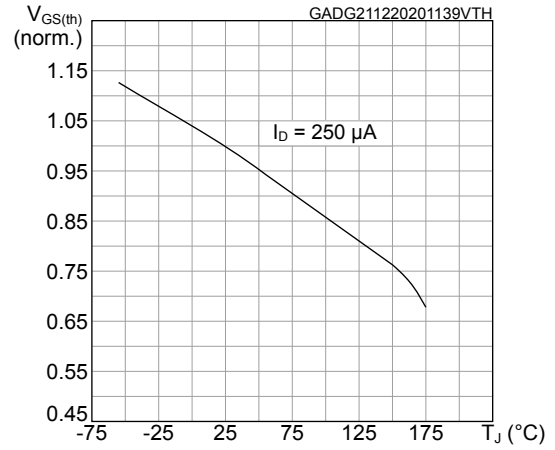


Figure 9. Normalized on-resistance vs temperature

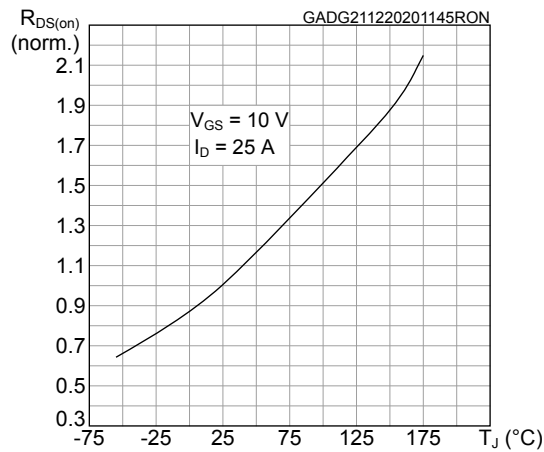


Figure 10. Normalized V_(BR)DSS vs temperature

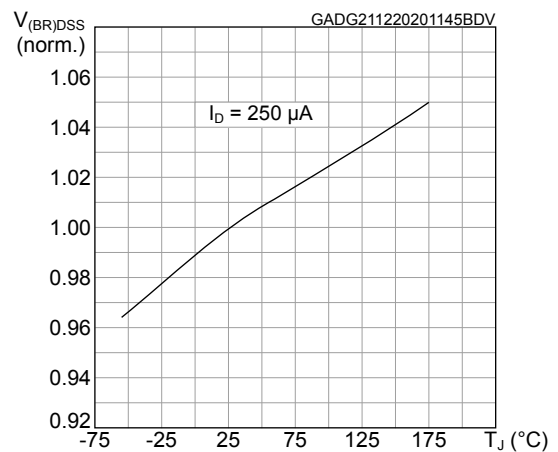
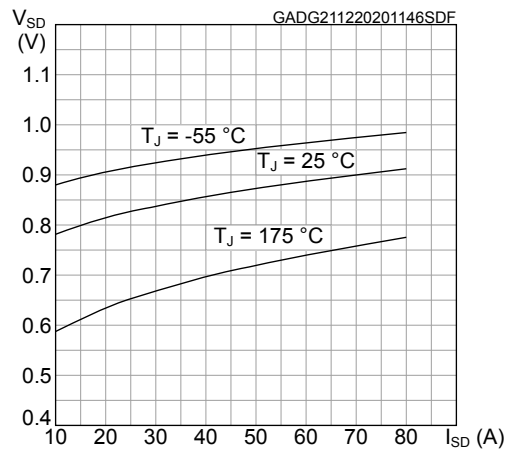
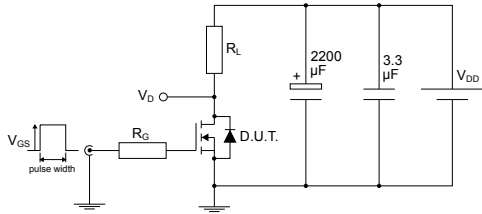


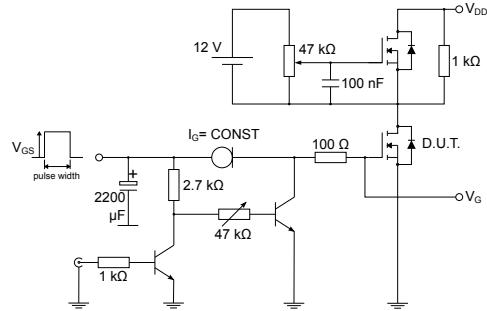
Figure 11. Typical reverse diode forward characteristics



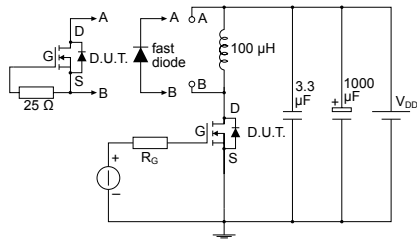
3 Test circuits

Figure 12. Test circuit for resistive load switching times


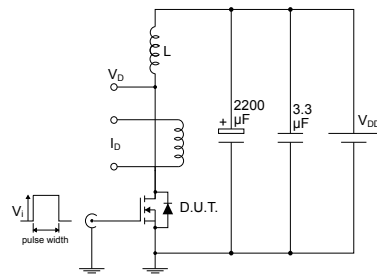
AM01468v1

Figure 13. Test circuit for gate charge behavior


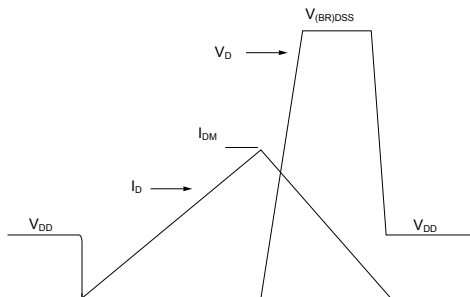
AM01469v1

Figure 14. Test circuit for inductive load switching and diode recovery times


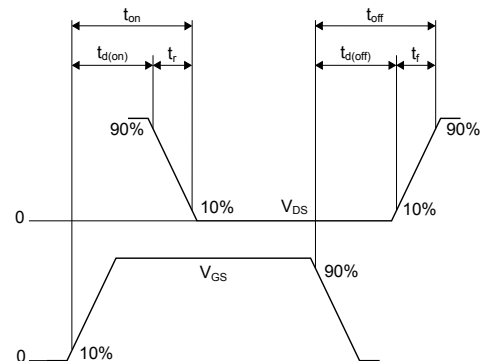
AM01470v1

Figure 15. Unclamped inductive load test circuit


AM01471v1

Figure 16. Unclamped inductive waveform


AM01472v1

Figure 17. Switching time waveform


AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 PowerFLAT 5x6 WF type C package information

Figure 18. PowerFLAT 5x6 WF type C package outline

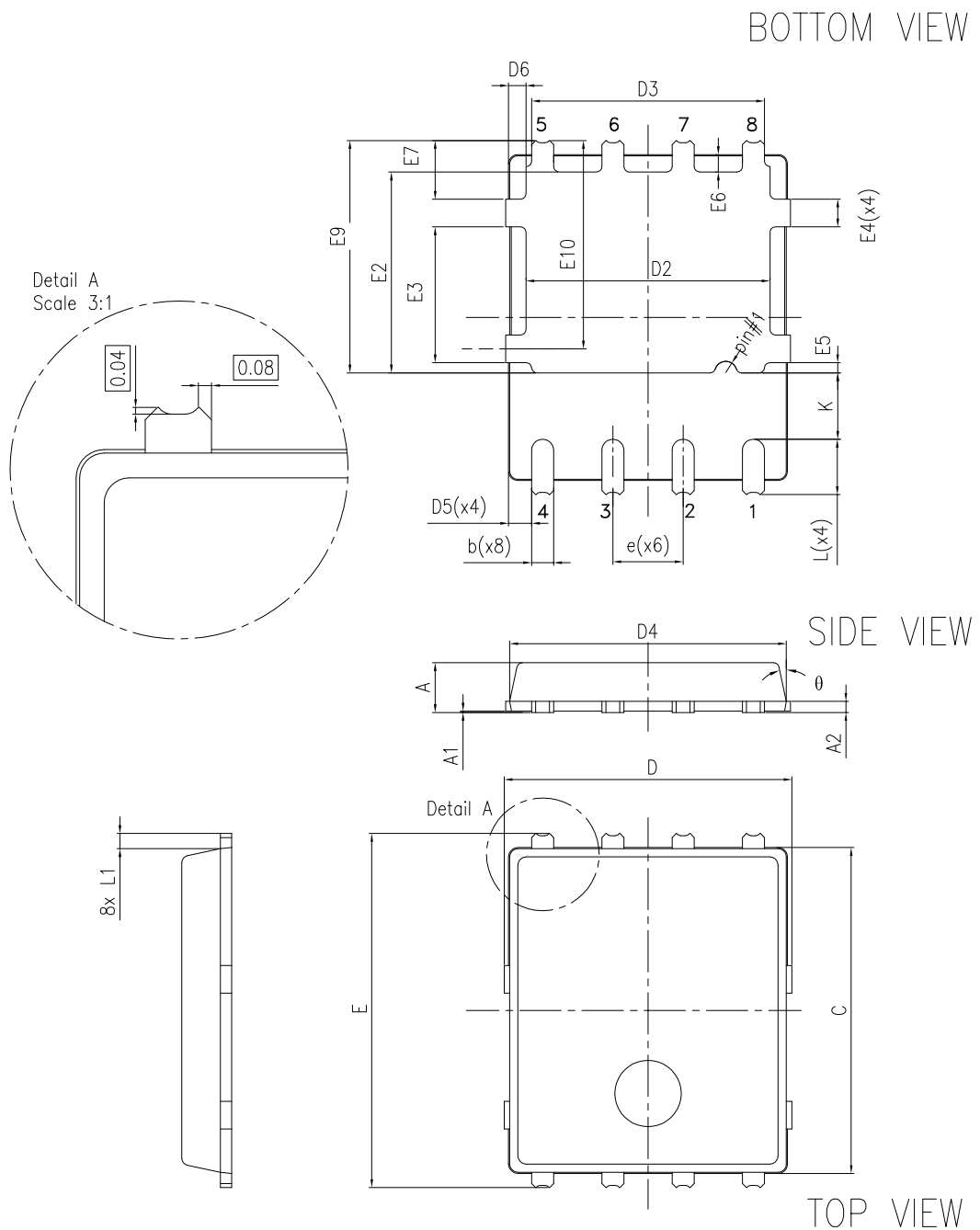
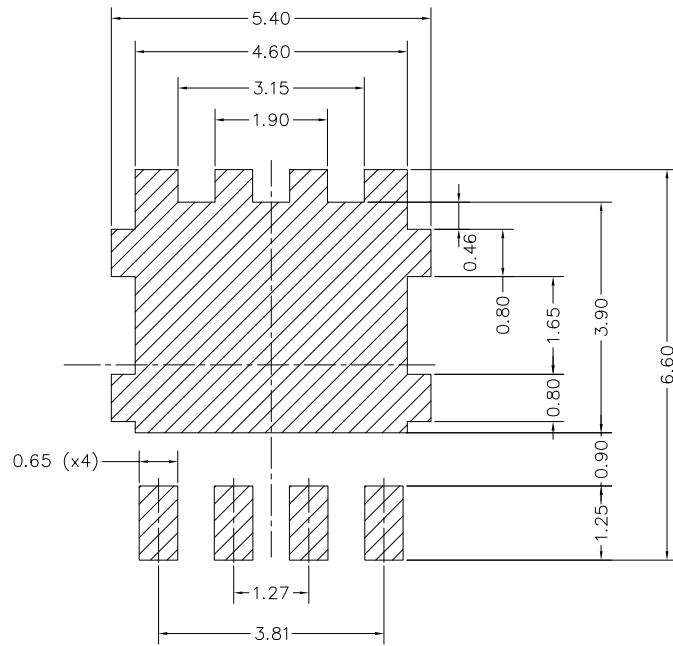


Table 7. PowerFLAT 5x6 WF type C mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.00		0.05
A2		0.25	
b	0.30		0.50
C	5.80	6.00	6.10
D	5.00	5.20	5.40
D2	4.15		4.45
D3	4.05	4.20	4.35
D4	4.80	5.00	5.10
D5	0.25	0.40	0.55
D6	0.15	0.30	0.45
e		1.27	
E	6.20	6.40	6.60
E2	3.50		3.70
E3	2.35		2.55
E4	0.40		0.60
E5	0.08		0.28
E6	0.20	0.325	0.45
E7	0.85	1.00	1.15
E9	4.00	4.20	4.40
E10	3.55	3.70	3.85
K	1.05		1.35
L	0.90	1.00	1.10
L1	0.175	0.275	0.375
θ	0°		12°

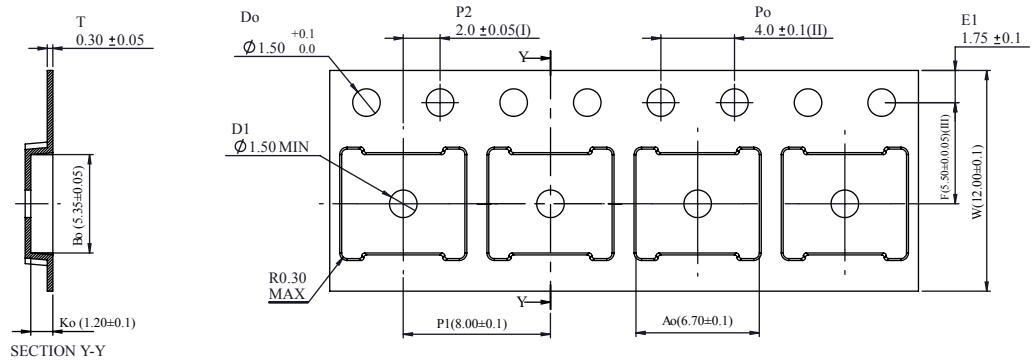
Figure 19. PowerFLAT 5x6 recommended footprint (dimensions are in mm)



8231817_FOOTPRINT_rev20

4.2 PowerFLAT 5x6 WF packing information

Figure 20. PowerFLAT 5x6 WF tape (dimensions are in mm)



- (I) Measured from centreline of sprocket hole to centreline of pocket.
- (II) Cumulative tolerance of 10 sprocket holes is ± 0.20 .
- (III) Measured from centreline of sprocket hole to centreline of pocket.

Base and bulk quantity 3000 pcs

8234350_TapeWF_rev_C

Figure 21. PowerFLAT 5x6 package orientation in carrier tape

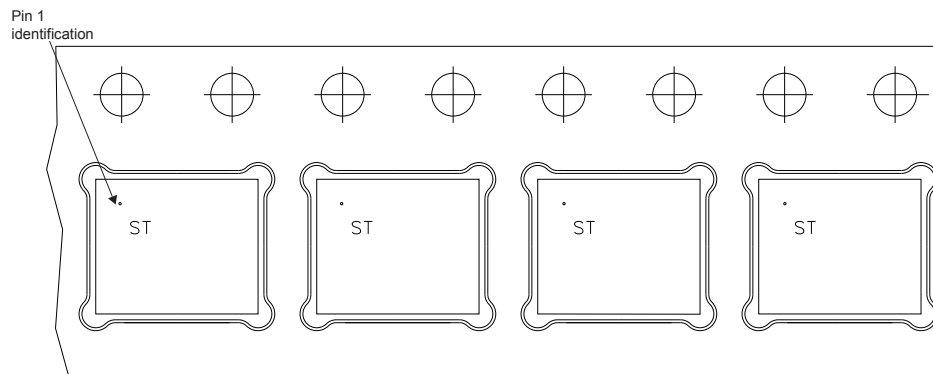
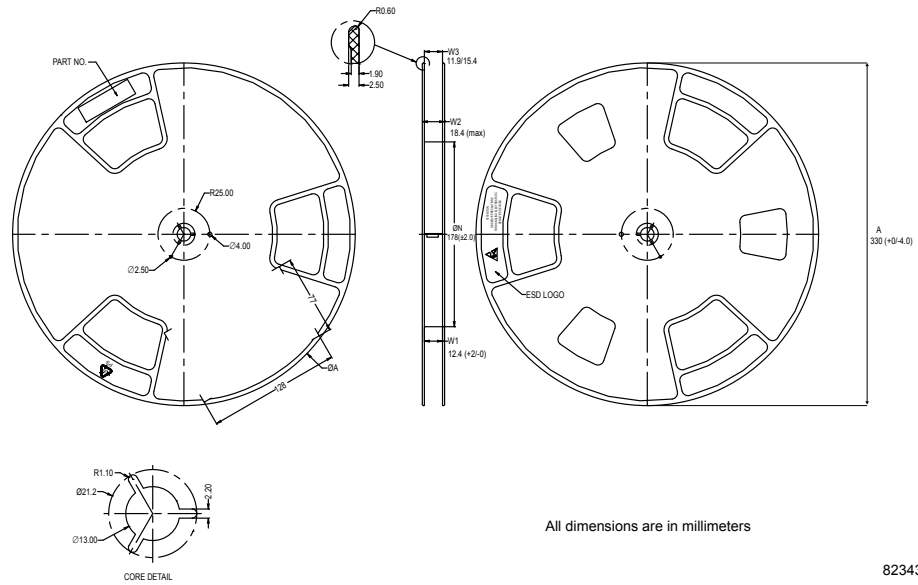


Figure 22. PowerFLAT 5x6 reel (dimensions are in mm)



Revision history

Table 8. Document revision history

Date	Version	Changes
04-Jan-2021	1	First release.
08-Mar-2021	2	Updated Table 1. Absolute maximum ratings.

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